



#12
RCE
y Robinson
7/24/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: 10/045,137 Confirmation No.: 3416
First Named Inventor: Wang, Albert Z. H. Filing Date: 23 October 2001
Group Art Unit: 2811 Examiner: Hu, S.
Atty. Docket No.: NS-3868-2C US
Title: Dual Direction Over-Voltage And Over-Current IC Protection Device And Its Cell Structure
Assignee(s): National Semiconductor Corporation

Mountain View, California
10 June 2003

**MAIL STOP RCE
COMMISSIONER FOR PATENTS
PO Box 1450
Alexandria, Virginia 22313-1450**

**REQUEST FOR CONTINUED EXAMINATION
UNDER 37 CFR 1.114**

Sir:

This is a Request for Continued Examination ("RCE") of the above patent application under 37 CFR 1.114.

Please enter and/or consider the following document which is enclosed or was previously submitted: Amendment, dated 10 June 2003.

The RCE fee required under 37 CFR 1.17(e) is authorized in an accompanying transmittal letter.

Please telephone Attorney for Applicant(s) at 650-964-9767 if there are any questions.

EXPRESS MAIL LABEL NO.:

ER 070 767 528 US

Respectfully submitted,

Ronald J. Meetin

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Attorney for Applicant(s)
Reg. No. 29,089

210 Central Avenue
Mountain View, CA 94043-4869

2003-06-10 RCE.doc

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10 June 2003

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2811

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Re: Application No.: 10/045,137 Confirmation No.: 3416
First Inventor: Albert Z.H. Wang Filing Date: October 23, 2001
Group Art Unit: 2811 Examiner: Hu, S.
Atty. Docket No.: NS-3868-2C US
Title: Dual Direction Over-Voltage And Over-Current IC Protection Device And Its Cell Structure
Assignee: National Semiconductor Corporation

Sir:

Transmitted herewith are the following documents for the above patent application:

- (1) Return Receipt Postcard;
- (2) This Transmittal Letter (in duplicate);
- (3) RCE (1 pp.);
- (4) Amendment (13 pps.);
- (5) Appendix (4 pps.); and
- (6) Gray ref.

The fee has been calculated as shown below:

CLAIMS AS AMENDED

Claims Remaining <u>After Amendment</u>	Highest No. <u>Previously Paid For</u>	Present <u>Extra</u>	Rate	Additional Fee
Total Claims 25	Minus 20	= 5	x \$18.00	\$ 90.00
Independent Claims 3	Minus 3	= 0	x \$84.00	\$ 0.00
<input type="checkbox"/> Fee of \$280 for the first filing of one or more multiple dependent claims				\$ 0.00
<input type="checkbox"/> Fee for Request for Extension of Time (month(s))				\$ 0.00
<input checked="" type="checkbox"/> Fee for Request for Continued Examination				\$ 750.00
Total additional fee for this Amendment:				\$ 840.00
<input checked="" type="checkbox"/> Please charge Deposit Account No. 502641 in the amount of				\$ 840.00
<input checked="" type="checkbox"/> Conditional Petition for Extension of Time: If an extension of time is required, the Commissioner is authorized to deduct the necessary fee from Deposit Account No. 502641.				
<input checked="" type="checkbox"/> Also, charge any additional fees required and credit any overpayment to Deposit Account No. 502641.				
<input type="checkbox"/> Enclosed is a check in the amount of			\$	

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Respectfully submitted,

Ronald J. Meetin

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#10P (NE)
Amend C
Y Robinson
7/2/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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First Named Inventor: Wang, Albert Z. H. Filing Date: 23 October 2001
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AMENDMENT

Sir:

Responsive to the Office Action mailed 11 March 2003, please amend the above patent application as follows:

IN THE CLAIMS

Amend Claims 2, 3, and 5 - 8 to read:

C1

--2. (Twice amended) The ESD protection structure of Claim 8, wherein said first conductivity type is n-type, and said second conductivity type is p-type.

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3. (Twice amended) The ESD protection structure of Claim 8, wherein said first conductivity type is p-type, and said second conductivity type is n-type.

C2

5. (Three times amended) The ESD protection structure of Claim 8, wherein said third semiconductor region includes a well region of said first conductivity type formed in a semiconductor substrate of said second conductivity type.